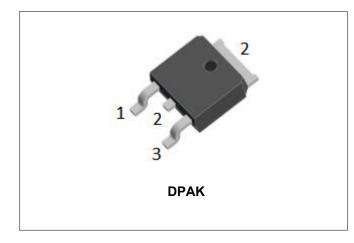


6CWQ20FN

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6CWQ20FN SCHOTTKY RECTIFIER



Features

- 200°C TJ operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- "-A" is an AEC-Q101 qualified device
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Disk drives
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

Maximum Ratings(Tc =25°C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage			200	N
Working Peak Reverse Voltage DC Blocking Voltage	V _{RWM} V _R	-	200	V
		50% duty cycle $@T_c = 131^{\circ}C$,	3.5(peg leg)	^
Average Rectified Forward Current	I _F (AV)	rectangular wave form	7(peg device)	A
Peak One Cycle Non-Repetitive Surge Current(peg leg)	I _{FSM}	8.3 ms, half Sine pulse	84	А

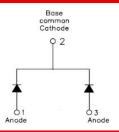
Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 3A, Pulse, T _J = 25 °C	0.84	0.89	V
(per leg) *	V _{F2}	@ 3A, Pulse, TJ = 125 °C	0.69	0.71	V
Reverse Current (per leg) *	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.001	1	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	0.3	5	mA
Junction Capacitance (per leg)	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	54	60	pF
Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	5.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

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Circuit Diagram





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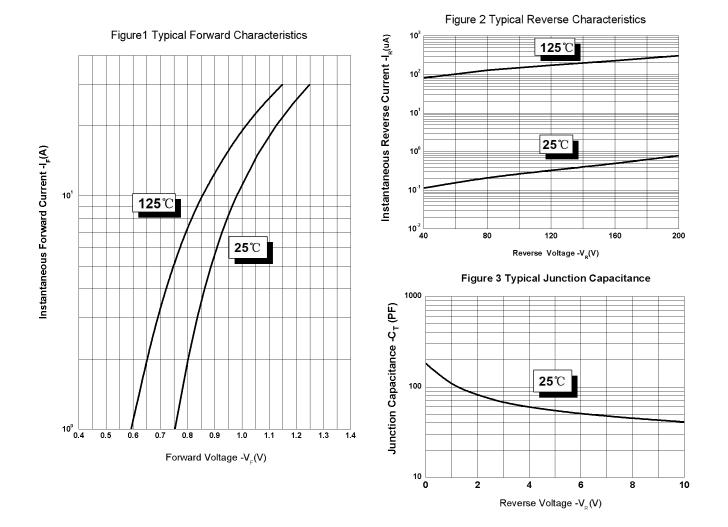
RoHS 🕅

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +200	°C
Storage Temperature	T _{stg}	-	-55 to +200	°C
Typical Thermal Resistance Junction to	B		4.7(peg leg)	°C/W
Case	$R_{\theta JC}$	-	2.35(peg device)	0/00
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

Ratings and Characteristics Curves



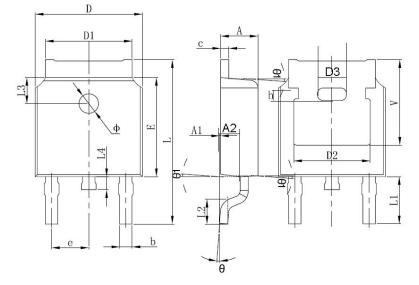


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Mechanical Dimensions DPAK



The outline from different package houses may have slight differences. So the outline above is just schematic. The dimensions are controlled per specifications.

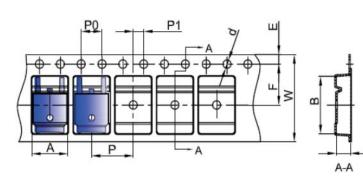
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	2.18	-	2.39
A1	-	-	0.13
b	0.64	-	0.89
с	0.46	-	0.89
D	6.35	-	6.73
D1	4.95	-	5.46
D2	4.32	-	-
E	5.97	6.1	6.22
е	2.29BSC		
L	9.4	-	10.41
L1	2.90 REF.		
L2	1.4	1.52	1.78
L3	1.60 REF.		
L4	-	-	1.02
Φ	1.1	-	1.3
Θ	0°	-	10°
V	5.21	-	-

Ordering Information

Device	Package	Shipping
6CWQ20FN	DPAK (Pb-Free)	2500pcs / reel
6CWQ20FNTR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

Carrier Tape Specification DPAK



SYMBOL	Millimeters		
STMBOL	Min.	Max.	
A	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Φ1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

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Marking Diagram



Where XXXXX is YYWWL

6 CW

Q

20 FN

SSG

YΥ

L

ww

- = Forward Current (7A)
 - Configuration
 Device Type
 - = Reverse Voltage (200V)
 - = Package type = SSG
 - = Year
 - = Week
 - = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0



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